

Index

A

- Absorption coefficient, 18–19, 47, 76
- Auger mechanism
 - Auger 1, 53–57, 78, 166–167
 - Auger 7, 53–57, 77, 167
 - Auger S, 53–57, 105
 - Auger lifetime, 54, 78–79, 166–169
 - Auger suppression, 263
- Avalanche photodiodes, 94–97
 - avalanche multiplication, 95, 131
 - ionization ratio, 94
 - ionization coefficient, 95

B

- Background-limited performance (BLIP), 19–22, 175
- Bandgap energy
 - bandgap alloys, 44
 - bowing parameter, 47–49
 - InAsSb, 47–49
 - InGaAsSb, 51, 98
 - superlattice bandgap, 71–73, 82, 113
 - Varshni relation, 44
- Bandgap engineering, 4, 65, 176
- Band offset, 64, 70–71, 82, 141–142, 156
- Barrier detectors, 141–179, 221, 248
 - blocking layer, 8
 - complementary barrier, 156, 159
 - current density, 143, 150, 161
 - unipolar barrier, 141–143, 145–147, 153

Blocked impurity band (BIB)

- detectors, 7–8, 17
- Bolometers, 11–13, 16, 235, 266
- Burstein-Moss effect, 46

C

- Carrier lifetime
 - in HgCdTe, 77–80
 - in InAs, 56
 - in InAsSb, 57
 - in InSb, 54
 - in superlattices, 78–79, 82
- Carrier mobility
 - in alloy, 43, 45–46
 - in InAsSb, 51, 152
 - in superlattices, 74
- Cold shield, 24, 171
- Conduction band offset, 124, 147
- Crystal growth, 33–37

D

- Dark current density, 166–171
 - depletion layer current, 144, 163–164, 166
 - diffusion current, 143–144, 146, 164
 - in p-n junction, 163
 - in HgCdTe photodiodes, 262–263
 - in InAsSb detectors, 149–150,
 - in superlattice detectors, 115–116, 118, 120–121, 161
 - surface leakage current, 9, 96, 116, 127, 142
 - tunneling current, 74, 82, 145

- Detectivity, 14–15, 18–21, 25–27
of cascade infrared detectors, 187, 192, 196
of dual-band detectors, 252
of IR detectors, 92
of HgCdTe photodiodes, 198
of InAsSb detectors, 99, 103, 106, 153
of superlattice systems, 83, 123, 125
of triple-band detectors, 253
Johnson noise limited, 120, 187, 192
- Dielectric constant, 43, 45
- Dispersion equation, 208
- Double heterojunction, 112, 119, 154–155
- E**
- Effective mass, 43–45, 49, 73–74
- Electromagnetic spectrum, 9, 210
- Electron barrier, 154, 156, 159, 189–190, 194–195
- Epitaxial growth, 38–41
- Extrinsic detectors, 7, 19
- F**
- Field of view, 20, 232
- Fill factor, 205, 217, 219
- Fixed pattern noise, 26
- Focal plane arrays (FPAs), 21–22, 227–253, 262–264
- G**
- GaAs substrates, 69, 163, 197
- Ga-free superlattices, 68, 75–76, 78, 80–83
- GaSb/AlSb superlattices, 64, 189–190
- GaSb, 32–37, 43–45
- GaSb substrates, 34–35, 69, 98, 259
- Graded bandgap, 154, 159
- Generation-recombination noise, 20
- Generation recombination processes, 52–57, 76, 115
- Generation recombination rates, 18
- Golay cell, 13, 16
- H**
- Hemispherical lens, 197, 205
- Heterojunction, 75, 112, 121, 189, 249, 261
- HgCdTe microstructures, 218–220
- HgCdTe photodetectors, 16–17, 19, 90, 97, 117, 121–123, 147, 170–172, 188, 196–199, 260–263
- HgCdTe properties, 74, 76–81, 165–166, 265
- Hg-vacancy doped, 77
- Hole barrier, 156, 159, 189, 194–195
- Homojunction, 99, 121, 131, 160, 250
- Hyperhemispherical lens, 100, 205
- I**
- Impact ionization, 53, 94–97
- Ionization ratio, 94
- Ionization coefficient, 95
- InAs, 31, 36–37, 42–43, 45, 54–56, 70–71, 75
- InAs detectors, 92–98, 144–147, 214
- InAsSb, 37, 44–51, 54, 57, 75–76
- InAsSb detectors, 98–107, 147–155, 166–170, 215, 220–223
- InAsSb FPAs, 242–245
- InAs/AlSb superlattices, 153, 155–156, 190
- InAs/GaSb superlattice detectorts, 112–123, 130–132
- InAs/GaSb superlattice FPAs, 245–253
- InAs/GaSb superlattices, 6, 66, 70–75, 79, 81–83, 155–157, 160–162, 168–171, 176–179, 188–199
- InAs/InAsSb superlattice detectorts, 123–129, 161

- InAs/InAsSb superlattices, 68,
75–76, 78, 80–83
- InAs/InGaSb superlattice
detectors, 112, 155
- InAs/InGaSb superlattices, 68–69, 72
- Infrared detectors
classification, 5–12
history, 2
photon detectors, 5–8
thermal detectors, 5–6, 10–13, 16
- InSb, 32–37, 42–47, 54–56, 79–80, 89
- InSb detectors, 90–92
- InSb FPAs, 238–242
- Interband cascade IR detectors
(IB CIDs), 188–198
- Interband cascade laser structures, 81
- Intrinsic carrier concentration, 45, 50
- Interband tunneling, 189–190
- J**
- Jet Propulsion Laboratory (JPL), 159
- Johnson noise, 187
- L**
- Lattice constant, 31, 43, 45, 67
- Lattice-matched emiconductors,
31–32, 67, 71, 142
- Lead salts, 16
- M**
- Metal organic chemical vapor
deposition (MOCVD), 37–42, 68
- Micro lenses, 204–205
- Minibands, 5, 71–72, 112, 189–190
- MIS photodiode, 9
- Modulation transfer function
(MTF), 21–22, 218, 234, 236, 242
- Molecular beam epitaxy (MBE),
37–42, 68–69, 91
- “M” structure, 153–155
- Multicolor detectors, 158, 176–177,
249, 252
- Multiple quantum wells, 63–64, 111
- N**
- nBn Detector FPAs, 242–246
- nBn structure, 9, 117, 132, 134–135,
141–152, 155, 158, 163, 169–171,
221–222, 265
- nBp structure, 155
- Noise equivalent temperature
difference (NEDT), 21–27, 151,
171–176, 218, 234–235, 247, 251
- Noise equivalent flux, 23
- Noise equivalent irradiance (NEI), 23
- Noise equivalent power (NEP),
14–15
- Noise mechanisms
 $1/f$ noise, 132–135
fixed pattern noise, 26
generation-recombination noise, 20
Johnson noise, 187
photon noise, 19, 26, 175
shot noise, 19–23, 187
spatial noise, 26
- “N” structure, 154
- O**
- Operability, 151, 239–240
- Optical concentrator, 17, 204
- Optical excitation processes, 6
- Optical immersion, 205
optically immersed
photodetectors, 163, 197–198
- Optics f-number, 25, 232, 234–237
- Optics MTF, 21–22, 234
- P**
- Passivation, 124, 126–129, 133
- Photovoltaic detectors, 8, 20, 92,
186, 192
- pBiBn detector, 156
- pBn structure, 145, 158–159
- pBp structure, 145, 154, 157,
160–162, 177–179, 248
- Photoconductive detectors, 2, 16,
20, 92

- Photoconductive gain, 192
 Photocurrent, 94, 115, 142–148
 Photon detectors, 5–8
 Photon flux density, 19–20
 Photon noise, 19, 26, 175
 Photonic crystals, 212–216
 Photon trapping detectors, 217–222
 p-i-n photodiodes, 116–119, 121, 130–132, 246, 261
 Planck's photon emittance, 20
 Plasmonic, 206–217
 Pyroelectric detectors, 11–13, 16
- Q**
 Quantum dot infrared photodetectors (QDIP), 214
 Quantum efficiency, 15–21, 106, 203, 217
 in p-i-n photodiode, 121–122, 125
 in pB_pp detector, 162
 in cascade infrared detectors, 192
 Quantum well, 5–6, 81
 multiple quantum wells, 63–64, 111
 Quantum well infrared photodetectors (QWIPs), 16, 19, 66, 186, 215, 266
 Quantum cascade infrared detectors (QCIDs), 186–188, 193, 196
- R**
 R_0A product, 106, 127
 of HgCdTe photodiodes, 117, 196–197
 of InAs photodiodes, 146
 of InAsSb photodiodes, 99, 101, 104–105
 of superlattice photodiodes, 83, 117, 120, 122, 191
 Radiative mechanism, 52–56, 77
 Raytheon Vision Systems' (RVS), 239
 Readout circuits, 175
 Response time, 193–194, 197–199
 Responsivity, 6, 14
 “Rule 07”, 146–148, 161, 166, 172–174, 262
- S**
 Scattering mechanisms, 45–46, 51, 74
 Scene contrast, 24, 27, 171, 234
 Schottky-barrier photodiode, 9
 Shockley-Read-Hall (SRH) mechanism, 52–56, 77–80, 142, 144, 164, 166–170, 261–262, 265
 Shot noise, 19–23, 187
 Signal flux, 23–24
 Signal-to-noise ratio (SNR), 14, 187
 Self-passivation, 142, 154
 Spatial noise, 26
 Spin-orbit splitting, 49–50
 Superlattices, 64–66, 68, 70–76, 78–79, 83–88, 155–157, 160–162, 168–171, 176–179, 188–199
 Surface current, 126–128, 142, 145–146
 Surface passivation, 124, 126–129, 133
 Surface plasmons (SP), 207–208, 211
 Surface traps, 133
 Systemic $1/f$ noise, 134
- T**
 Ternary alloys, 44–51
 Thermal detectors, 5–6, 10–13, 16
 Thermal generation rate, 18, 163, 166
 Thermopile, 11, 13
 Tunneling
 band-to-band tunneling, 145
 trap-assisted tunneling, 145
 Tunneling regions, 189–190, 194
 Two-color detectors, 158, 177, 252
 Three-color detectors, 176, 249
 Type-II superlattices (T2SLs), 64–66, 68, 70–76, 78–79, 83–88,

- 155–157, 160–162, 168–171,
176–179, 188–199
Type-II superlattice FPAs, 245–253
Type-III superlattices, 64–66
- U**
Uncooled detection, 24, 196, 204, 235
Unipolar barrier, 141–143, 145–147,
153
- V**
Valence band offset, 124, 141–142,
145–147, 156
- Vigo System, 198
Virtual crystal approximation
(VCA), 47, 50
- W**
Well capacity, 9, 22, 171
“W” structure, 153
- X**
XBn structure, 144, 154, 244
- Z**
Zero offset, 142



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